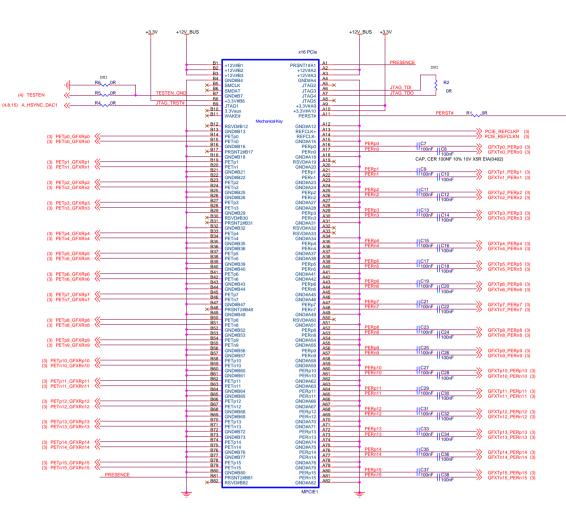


PCI-EXPRESS EDGE CONNECTOR



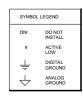
Power Sequence Circuit to ensure SMPS_EN is released after +12V_BUS and +3.3V_BUS are both in regulation. Pull-up may or may not be required on SMPS_EN signal depending on SMPS design.

Node 1 When +12V ramps above min Vbe, SMPS_EN will be helt low Node 2 When +3.3V gets close to regulation, one of the two conditions of releasing SMPS_EN is active

Target ~ 900mV when +3.3 at min regulation (worse case)
Typical trigger when +3.3V ramps above 2.2V (650mV)

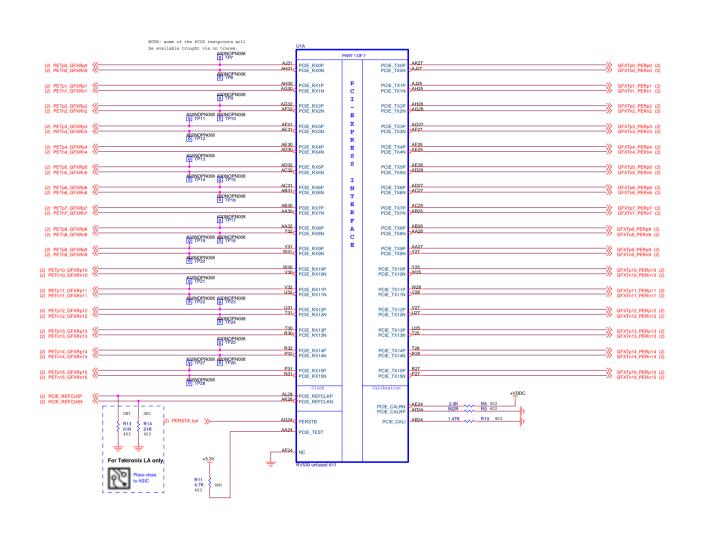
Node 3 When +12V gets close to regulation, one of the two conditions of releasing SMPS_EN is active

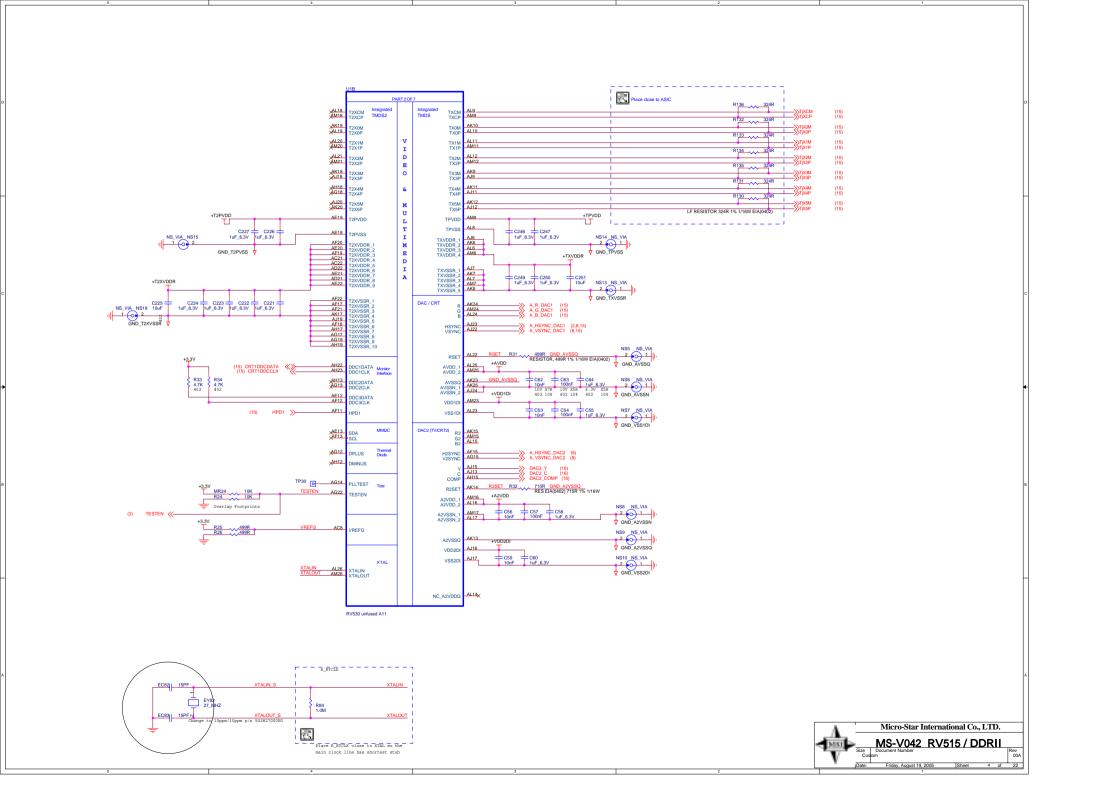
Target ~ 1.25V when +12 at min regulation (worse case)
Typical trigger when +12V ramps above 10V (1.1V)

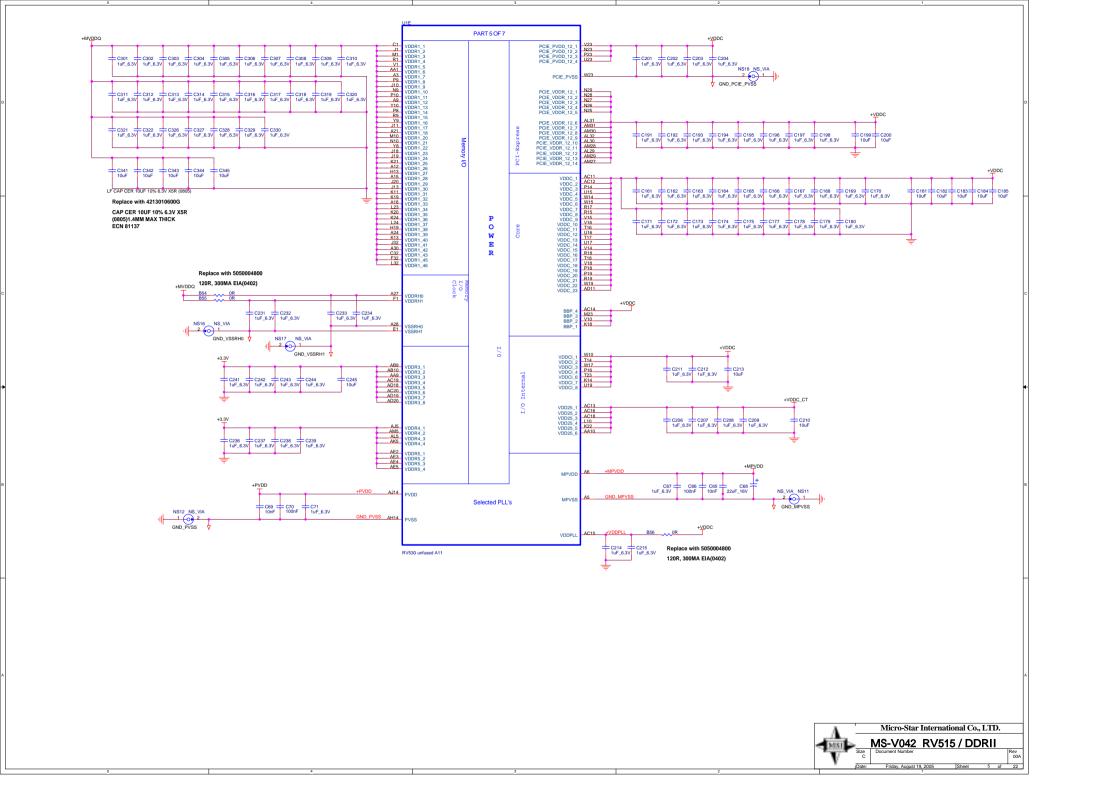


CAP CERAMIC 100NE 10% 10V X5R EIA(0402)

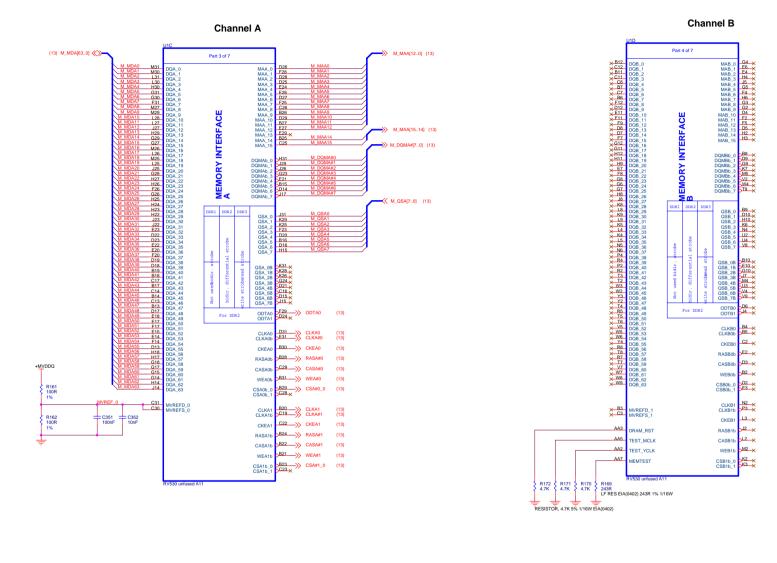




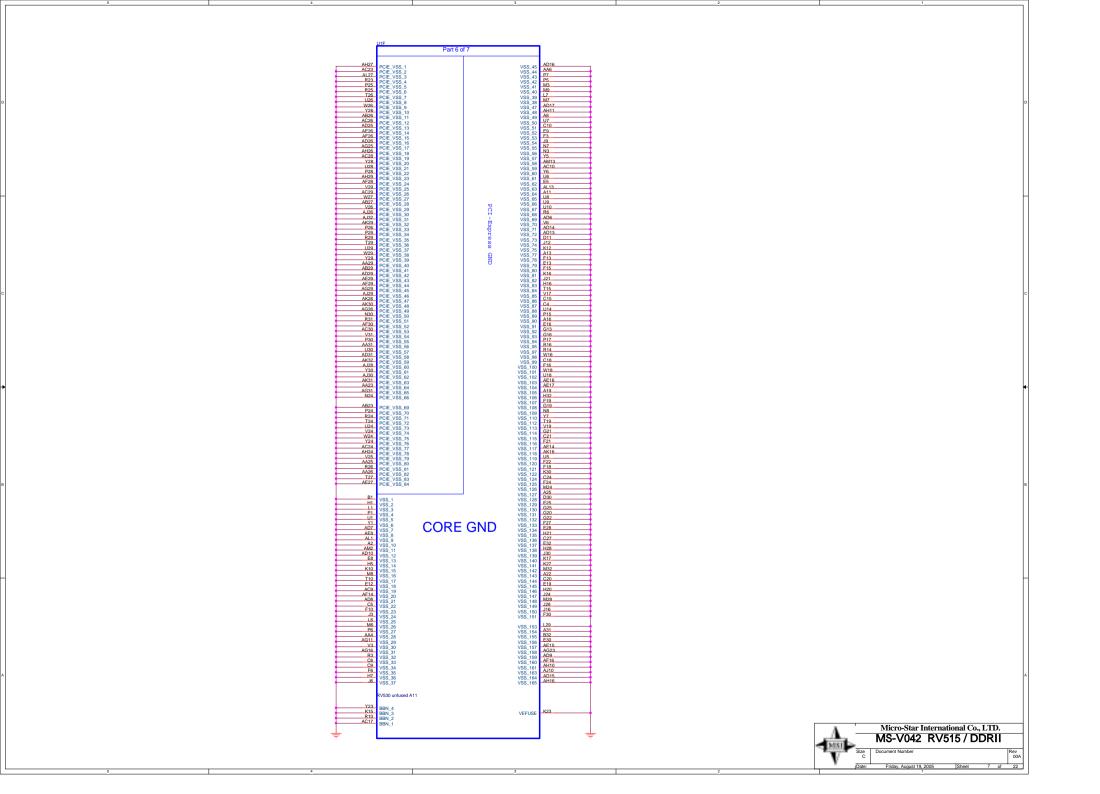


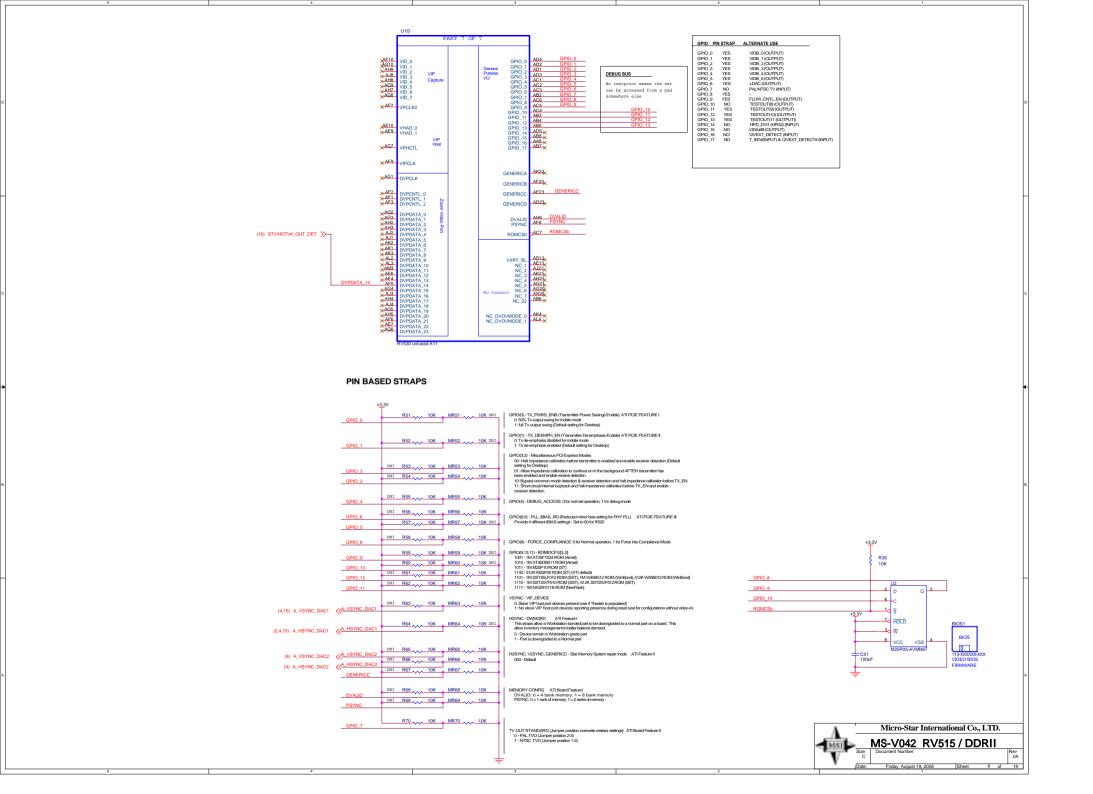


RV530 MEMORY CHANNELS A and B

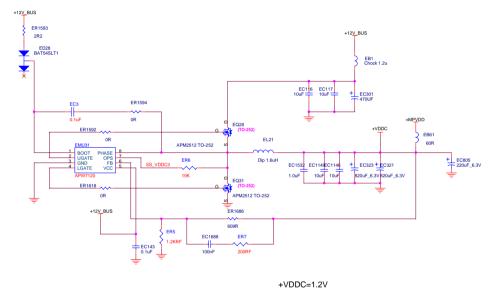


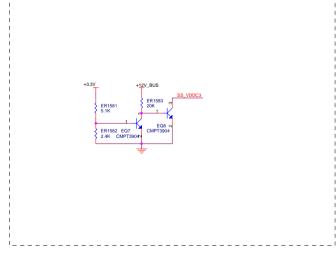




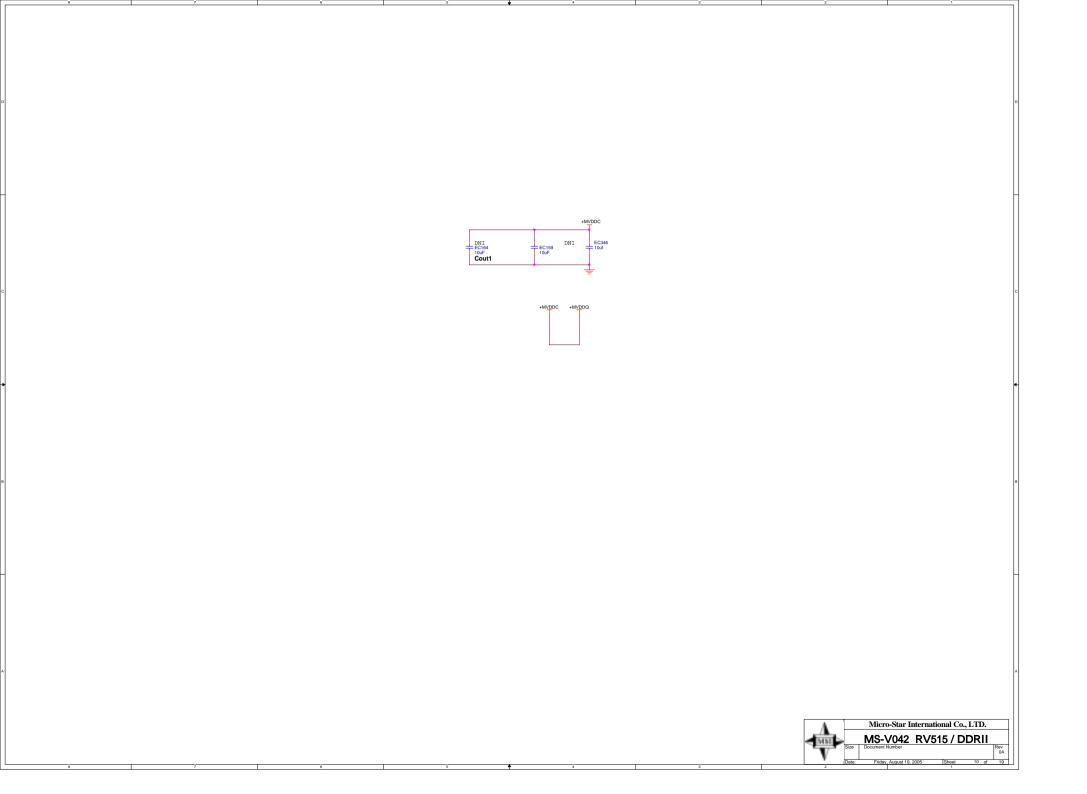


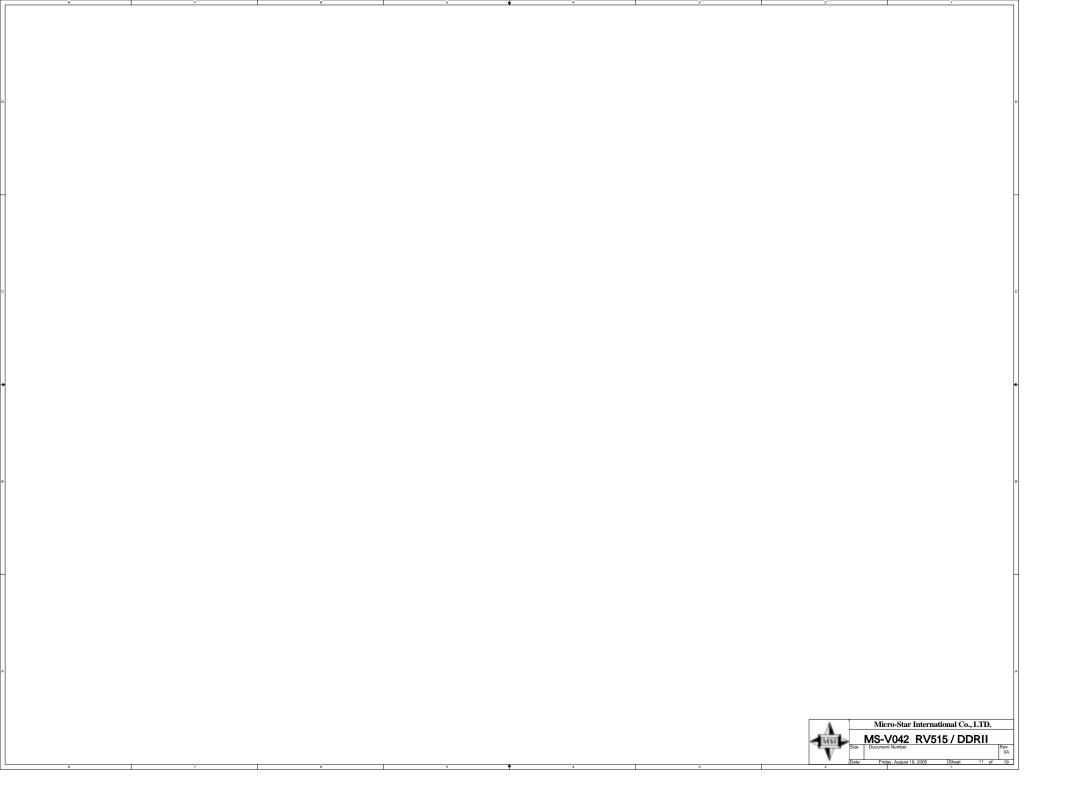
CORE REGULATOR +VDDC

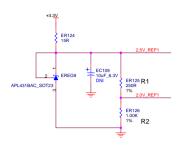


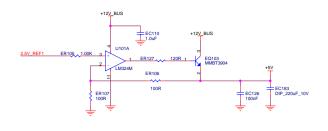


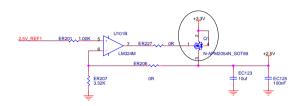
| Micro-Star International Co., LTD. | MS-V042 RV515 / DDRII | Szz | Document Number | Rev OA | DBME | Friday, August 19, 2005 | Sheet 9 of 19

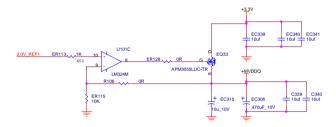














Replace with 5050004800 120R, 300MA EIA(0402)



CHANNEL A: RANK 0 128MB DDR2

